

STABISTORS

Diodes with controlled conductance in a all-glass DO-7 envelope intended for low voltage regulation in circuits for clipping, coupling, clamping, meter protection, bias regulation and in many applications which require tight tolerances and low voltage levels.
The series consists of 4 types with nominal voltages ranging from 1,4 to 3,6V with a tolerance of $\pm 5\%$.

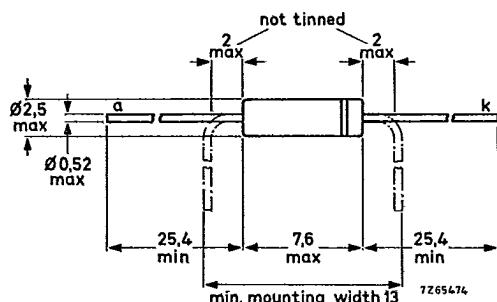
QUICK REFERENCE DATA

Regulation voltage range	V _F	nom.	1,4 to 3,6	V
Regulation voltage tolerance			± 5	%
Continuous reverse voltage	V _R	max.	10	V
Repetitive peak reverse voltage	V _{RRM}	max.	10	V
Repetitive peak forward current	I _{FRM}	max.	250	mA
Total power dissipation up to T _{amb} = 32 °C	P _{tot}	max.	400	mW
Operating junction temperature	T _j	max.	200	°C

MECHANICAL DATA

Dimensions in mm

DO-7



Cathode indicated by coloured band

T-11-21**RATINGS** Limiting values in accordance with the Absolute Maximum System (IEC134)

Continuous reverse voltage	V _R	max.	10	V
Repetitive peak reverse voltage	V _{RRM}	max.	10	V
Repetitive peak forward current	I _{FRM}	max.	250	mA
Total power dissipation up to T _{amb} = 32 °C	P _{tot}	max.	400	mW
Storage temperature	T _{stg}	-65 to +175	°C	
Operating junction temperature	T _j	max.	200	°C

THERMAL RESISTANCE

From junction to ambient in free air R_{th j-a} = 0,42 K/mW

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CHARACTERISTICS

 $T_j = 25^\circ\text{C}$ unless otherwise specified

	Regulation voltage		Temperature coefficient at $I_F = 1 \text{ mA}$	Differential resistance			
	$V_F (\text{V})$			$S_F (\text{mV/K})$	$r_{\text{diff}} (\Omega); f = 1 \text{ kHz}$		
	at $I_F = 1 \text{ mA}$	at $I_F = 10 \text{ mA}$			at $I_F = 1 \text{ mA}$		
BZX75-....	min.	max.	typ.		typ.		
C1V4	1,16	1,34	-4		60		
C2V1	1,75	2,05	-6		90		
C2V8	2,33	2,70	-8		120		
C3V6	3,02	3,45	-10		150		
	at $I_F = 10 \text{ mA}$		at $I_F = 10 \text{ mA}$		at $I_F = 10 \text{ mA}$		
	min.	nom.	max.	typ.	typ.	max.	
C1V4	1,33	1,40	1,47	-3,3	6	10	
C2V1	1,99	2,10	2,21	-5,0	9	15	
C2V8	2,66	2,80	2,94	-6,6	12	20	
C3V6	3,42	3,60	3,78	-8,2	15	25	

Reverse current

 $V_R = 5 \text{ V}$

$$\left. \begin{array}{l} \text{BZX75-C1V4} \\ \text{BZX75-C2V1} \end{array} \right\} I_R < 500 \text{ nA}$$

$$\left. \begin{array}{l} \text{BZX75-C2V8} \\ \text{BZX75-C3V6} \end{array} \right\} I_R < 200 \text{ nA}$$

Recovered charge when switched from

 $I_F = 10 \text{ mA}$ to $V_R = 5 \text{ V}$; $R_L = 500 \Omega$

$Q_s > 600 \text{ pC}$

Diode capacitance

 $V_R = 0; f = 1 \text{ MHz}$

$C_d < 250 \text{ pF}$

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